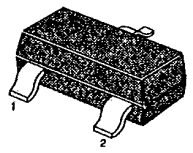
BCW60B NPN EPITAXIAL SILICON TRANSISTOR

T-29-19

GENERAL PURPOSE TRANSISTOR

SOT-23



1. Base 2. Emitter 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	32	V
Collector-Emitter Voltage	V_{CEO}	32	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	Tstg	150	°C

• Refer to MMBT3904 for graphs

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=2.0mA, I_B=0	32		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1.0μA, I_C=0	5		V
Collector Cutoff Current	I_{CES}	V_{CE}=32V, V_{BE}=0		20.	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0		20	nA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=10μA	20		
		V_{CE}=5V, I_C=2.0mA	180	310	
		V_{CE}=1V, I_C=50mA	70		
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=50mA, I_B=1.25mA		0.55	V
		I_C=10mA, I_B=0.25mA		0.35	V
Base-Emitter Saturation Voltage	V_{BE} (sat)	I_C=50mA, I_B=1.25mA	0.7	1.05	V
		I_C=50mA, I_B=0.25mA	0.6	0.85	V
Base-Emitter On Voltage	V_{BE} (on)	V_{CE}=5V, I_C=2.0mA	0.55	0.75	V
Current Gain-Bandwidth Product	f_T	I_C=10mA, V_{CE}=5V f=1 MHz	125		MHz
Output Capacitance	Cob	V_{CB}=10V, I_E=0 f=1.0MHz		4.5	pF
Noise Figure	NF	I_C=0.2mA, V_{CE}=5V R_S=2KΩ, f=1KHz		6	dB
Turn On Time	ton	I_C=10mA, I_{B1}=1mA		150	ns
Turn Off Time	toff	V_{BB}=3.6V, I_{B2}=1mA R_1=R_2=5KΩ, R_L=990Ω		800	ns

Marking